

Important notice

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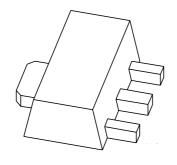
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PXTA14NPN Darlington transistor

Product data sheet Supersedes data of 1999 Apr 14 2004 Dec 09



NPN Darlington transistor

PXTA14

FEATURES

- High current (max. 500 mA)
- Low voltage (max. 30 V).

APPLICATIONS

• High input impedance preamplifiers.

DESCRIPTION

NPN Darlington transistor in a SOT89 plastic package. PNP complement: PXTA64.

MARKING

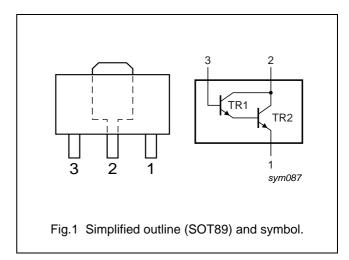
TYPE NUMBER	MARKING CODE ⁽¹⁾
PXTA14	*1N

Note

- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base



ORDERING INFORMATION

TYPE NUMBER	PACKAGE			
TIPE NOWIBER	NAME DESCRIPTION VER			
PXTA14	SC-62	plastic surface mounted package; collector pad for good heat transfer; 3 leads	SOT89	

NPN Darlington transistor

PXTA14

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	30	V
V _{CES}	collector-emitter voltage	V _{BE} = 0 V	_	30	V
V _{EBO}	emitter-base voltage	open collector	_	10	V
I _C	collector current (DC)		_	500	mA
I _{CM}	peak collector current		_	1	А
I _B	base current (DC)		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	1.3	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	ambient temperature		-65	+150	°C

Note

1. Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm². For other mounting conditions, see "Thermal considerations for the SOT89 in the General Part of associated Handbook".

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	96	K/W
R _{th(j-s)}	thermal resistance from junction to solder point		16	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm². For other mounting conditions, see "Thermal considerations for the SOT89 in the General Part of associated Handbook".

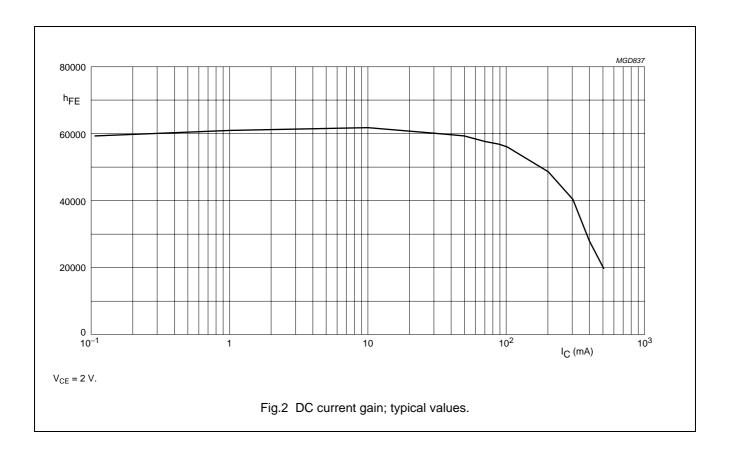
CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	I _E = 0 A; V _{CB} = 30 V	_	100	nA
I _{CES}	collector-emitter cut-off current	$V_{BE} = 0 \text{ V}; V_{CE} = 30 \text{ V}$	_	100	nA
I _{EBO}	emitter cut-off current	I _C = 0 A; V _{EB} = 10 V	_	100	nA
h _{FE}	DC current gain	$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}; \text{ (see Fig.2)}$	10000	_	
		I _C = 100 mA; V _{CE} = 5 V; (see Fig.2)	20000	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 100 \text{ mA}; I_B = 0.1 \text{ mA}$	_	1.5	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 100 \text{ mA}; I_B = 0.1 \text{ mA}$	_	1.5	V
V_{BEon}	base-emitter on-state voltage	$I_C = 100 \text{ mA}; V_{CE} = 5 \text{ V}$	_	2	V
f _T	transition frequency	$I_C = 30 \text{ mA}; V_{CE} = 5 \text{ V}; f = 100 \text{ MHz}$	125	_	MHz

NPN Darlington transistor

PXTA14



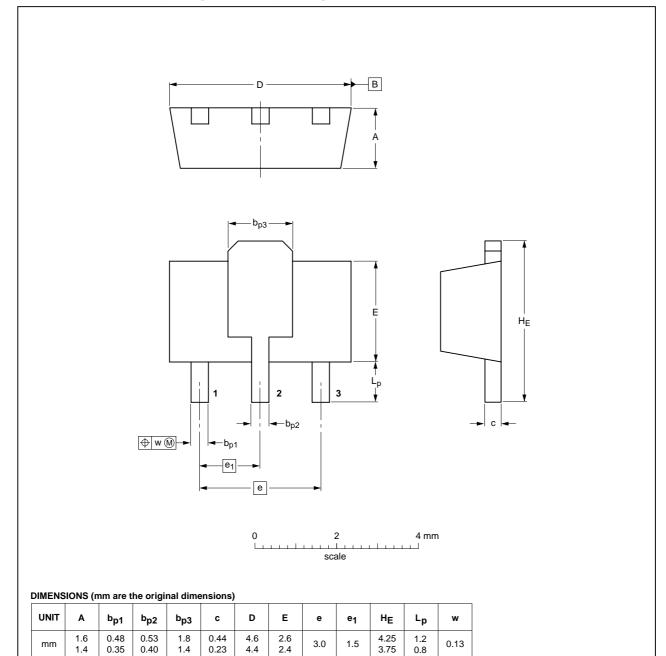
NPN Darlington transistor

PXTA14

PACKAGE OUTLINE

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



OUTLINE REFERENCES			EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT89		TO-243	SC-62			04-08-03 06-03-16

NPN Darlington transistor

PXTA14

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com
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